

ABSTRACT OF THE DISCLOSURE

There are provided a magnetoresistive device having excellent magnetic properties and a magnetic memory apparatus including this magnetoresistive device and which has excellent read and write characteristics.

A magnetoresistive device has an arrangement including a pair of ferromagnetic layers (magnetization fixed layer 5 and magnetization free layer 7) being opposed to each other through an intermediate layer 6 to obtain variations in magnetoresistance by an electric current flowing in the direction perpendicular to the film plane. This magnetoresistive device 1 has the pair of ferromagnetic layers 5, 7 composed of the magnetization fixed layer 5 made of a crystalline ferromagnetic layer provided under the intermediate layer 6 and the magnetization free layer 7 being made of an amorphous ferromagnetic layer being provided above the intermediate layer 6, and the magnetic memory apparatus is composed of this magnetoresistive device 1 and a bit line and a word line sandwiching the magnetoresistive device 1 in the thickness direction.